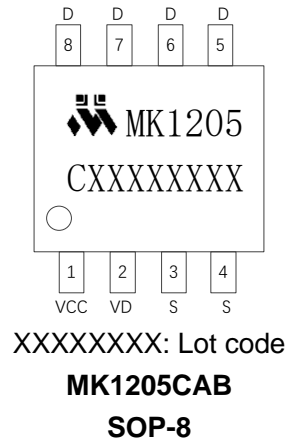




## 5. Ordering Information

Ordering No.	Description	Material
MK1205CAB	SOP-8, MSL-3, 4000 pcs/reel	Halogen free

## 6. Package Reference



### 6.1 Absolute Maximum Ratings <sup>(1)</sup>

VCC to S .....	-0.3V to +20V
D to S .....	-0.7V to 100V
VD to S .....	-1V to 115V
VD to S .....	-3V to 120V <sup>(2)</sup>
Continuous drain current $I_D$ .....	9A <sup>(3)</sup>
Pulsed drain current $I_{DM}$ .....	40A <sup>(4)</sup>
Continuous Power Dissipation. 2.5W ( $T_A = +25^\circ\text{C}$ ) <sup>(5)</sup>	
Junction Temperature .....	150°C

### 6.2 Recommended Operation Conditions

VCC to S.....	.5V to 9.5V
D to S.....	-0.7V to 90V
Maximum Junction Temp. ( $T_J$ ).....	+125°C

### 6.3 Thermal Resistance <sup>(6)</sup>

	$\theta_{JA}$	$\theta_{JC}$
SOP-8..	80	35 °C/W

#### Notes:

- (1) Exceeding these ratings may damage the device.
- (2) Repetitive pulse < 200ns
- (3)  $T_A = 25^\circ\text{C}$ : Calculated continuous current based on maximum allowable junction temperature
- (4) Repetitive rating: pulse width limited by maximum junction temperature
- (5) The maximum allowable power dissipation is a function of the maximum junction temperature  $T_J(\text{MAX})$ , the junction-to-ambient thermal resistance  $\theta_{JA}$ , and the ambient temperature  $T_A$ . The maximum allowable continuous power dissipation at any ambient temperature is calculated by  $P_D(\text{MAX}) = (T_J(\text{MAX}) - T_A) / \theta_{JA}$ . Exceeding the maximum allowable power dissipation will cause excessive die temperature.
- (6) Measured on JESD51-7, 4 layers PCB

## 7. Electrical Characteristics

$T_A=25^{\circ}\text{C}$ , unless otherwise noted.

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Internal MOS Section</b>						
Internal MOS Rdson	$R_{dson}$	$V_{CC}=9.5\text{V}$ , $I_d=1\text{A}$		10		m $\Omega$
Drain to Source Breakdown	$V_{DSS(BR)}$	$V_{CC}=V_D=0\text{V}$ , $I_d=250\mu\text{A}$	100			V
<b>Supply Management Section</b>						
VCC UVLO Rising	$V_{CC\_ON}$		4.3	4.6	4.9	V
VCC UVLO Falling	$V_{CC\_OFF}$		3.8	4	4.3	V
VCC UVLO Hysteresis	$V_{CC\_HYS\_T}$		0.25	0.6	0.75	V
VCC Regulation Voltage	$V_{CC\_REG}$	$V_D=14\text{V}$	8.2	9.1	10	V
Operating Current	$I_{CC}^{(6)}$	$V_{CC}=6\text{V}$ , $F_{sw}=100\text{kHz}$ ,	1.5	2.0	2.5	mA
Quiescent Current	$I_{q(VCC)}$	$V_{CC}=6.4\text{V}$ , $F_{sw}=0\text{Hz}$		350	550	$\mu\text{A}$
<b>Mosfet Voltage Sensing</b>						
$V_D-V_{SS}$ Adjusting Voltage	$V_{DS\_REG}$		-55	-40	-25	mV
Turn-On Threshold ( $V_D-V_{SS}$ )	$V_{ON\_th}$		-350	-300	-50	mV
Turn Off Threshold ( $V_D-V_{SS}$ )	$V_{OFF\_th}$			0	10	mV
Turn-On Propagation Delay	$T_{D\_on}$			25	40	ns
Turn-Off Propagation Delay	$T_{D\_off}$			10	15	ns
Turn On Blanking Time	$T_{B\_ON}$	$C_{LOAD}=2.2\text{nF}$	0.75	1.0	1.3	$\mu\text{s}$
Turn Off Blanking $V_{DS}$ Threshold in $T_{B\_ON}$	$V_{B\_OFF}$			2		V
Turn Off Blanking Time	$T_{OFF}$		250	300	350	ns
<b>Gate Driver</b>						
$V_G$ (Low)	$V_{G\_LOW}$	$V_{CC}=6.4\text{V}$ , $I_{LOAD}=0.1\text{A}$	0	0.2	0.4	V
$V_G$ (High)	$V_{G\_HIGH}$	$V_{CC}=6.4\text{V}$ , $I_{LOAD}=0.1\text{A}$	$V_{CC}-0.6$	$V_{CC}-0.3$	$V_{CC}$	V

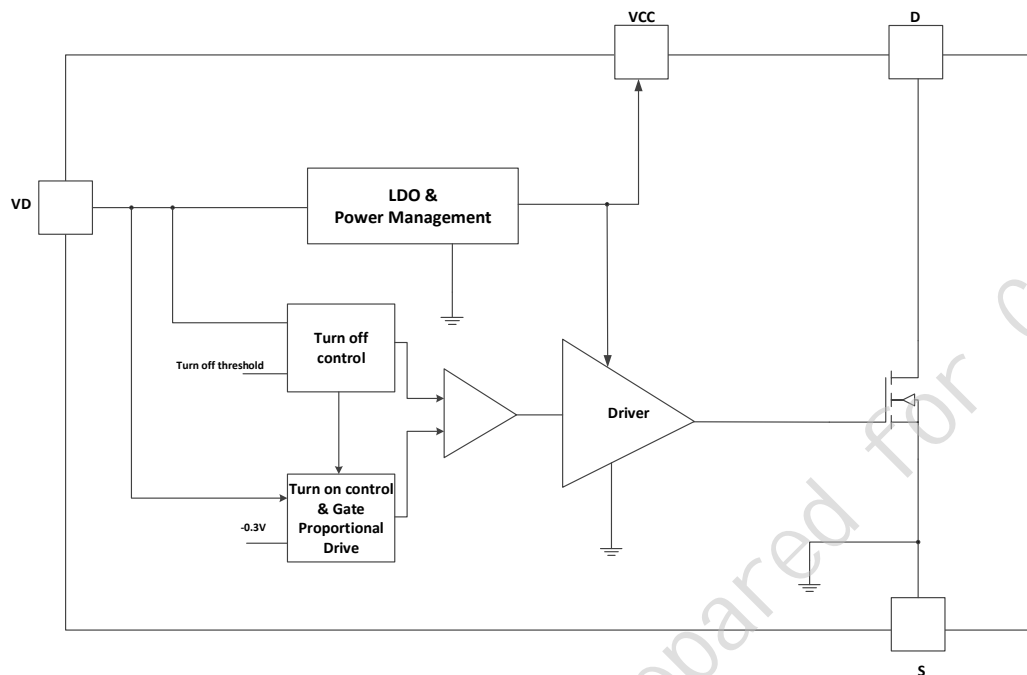
**Note:**

$I_{CC}$  in the table is the current consumed by the internal controller when 2.2nF load capacitance and 100kHz operating frequency.

## 8. Pin Functions

Pin #	Name	Description
1	VCC	Inner Regulator Output, supply MK1205
2	VD	FET drain voltage sense; HV pulse LDO input
3,4	S	Ground
5,6,7,8	D	FET drain

## 9. Block Diagram



**Figure 1. Functional Block Diagram**

## 10. Operation Descriptions

MK1205 is a high-performance synchronous rectifier which can replace the Schottky diode rectification in the flyback converter to improve efficiency, which supports DCM, CCM and QR operations. A great flexibility for system designing is brought by Self-supply which supports operations with both low-side rectification and high-side rectification without an auxiliary winding.

### 10.1. Conduction Phase

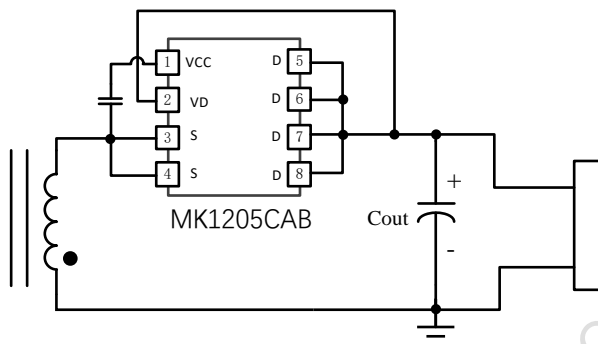
After SR VG turns on, a minimum blanking time  $T_{B\_ON}$  is required to prevent the parasitic ringing from falsely turning off SR VG. The minimum turn-on blanking time is around 1.0us for MK1205, during which the turn off threshold is increased to 2V. Right before  $T_{B\_ON}$  timer expires, MK1205 starts monitoring  $V_{DS}$  against a -40mV value to determine if internal VG needs to be slowly discharged. This operation adjusts  $V_{DS}$  of SR MOSFET to be around -40mV until the current through SR MOSFET drops to zero.

### 10.2. Turn off Phase

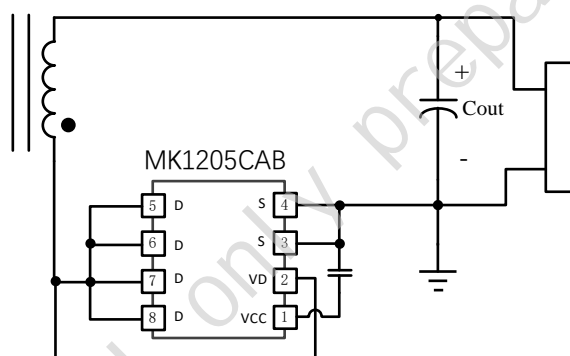
mk1205's turn-off threshold is different at different time. within the minimum turn-on blanking time  $t_{b\_on}$ ,  $V_{ds}$  turn-off threshold is 2v which is the same as  $v_{b\_off}$ . after the minimum turn-on blanking time  $t_{b\_on}$ , the turn-off threshold is around 0v, that combines with extremely fast 10ns turn-off propagation delay and 4a vg pull-down (sinking) current, synchronous rectifier is able to be turned off not too early which causes more sr fet body diode conduction time and more negative turn-off ringing, or not too late which creates risk of shoot through between primary side and sr side.

## 11. Typical Implementations

MK1205 supports both high side rectification and low side rectification to replace Schottky diode without the need of auxiliary winding as shown in Figure 2 and Figure 3. VCC is powered from pin VD and regulated at ~9V even when Vout is much lower than 5V. A 0.1uF bypass capacitor is suggested to regulate the bias voltage and reduce noise coupling from switching.

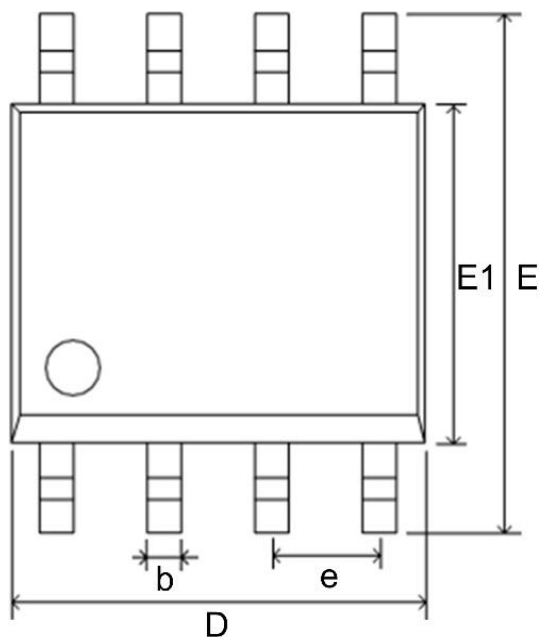


**Figure 2. The High side rectification**

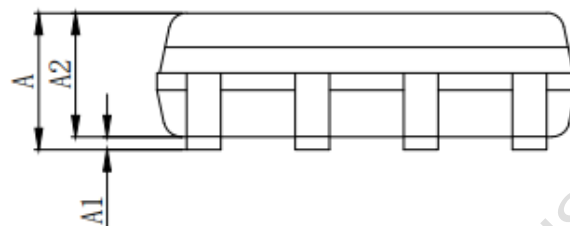


**Figure 3. The low side rectification**

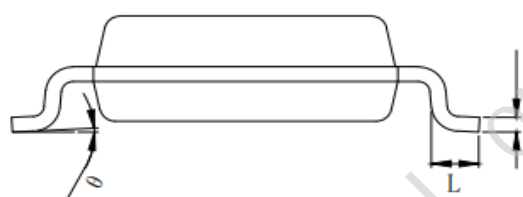
## 12. Package Information (SOP-8)



**Top View**



**Front View**



**Side View**

Symbol	Dimensions In Millimeters	
	MIN	MAX
A	1.3	1.75
A1	0.05	0.25
A2	1.25	1.65
b	0.33	0.51
c	0.2	0.25
D	4.7	5.1
E	5.8	6.2
E1	3.8	4.0
e	1.270(BSC)	
L	0.4	1.27
$\theta$	0°	8°